

SOT-23

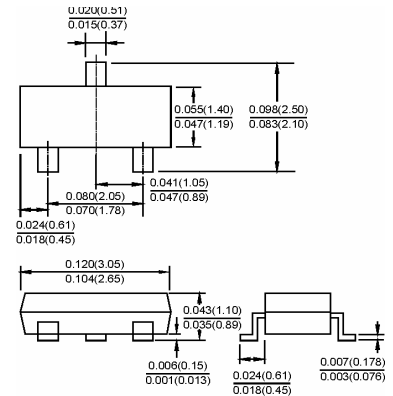


1. Base
2. Emitter
3. Collector

Features

Complimentary to SS8050

MARKING: Y2



MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Dimensions in inches and (millimeters)

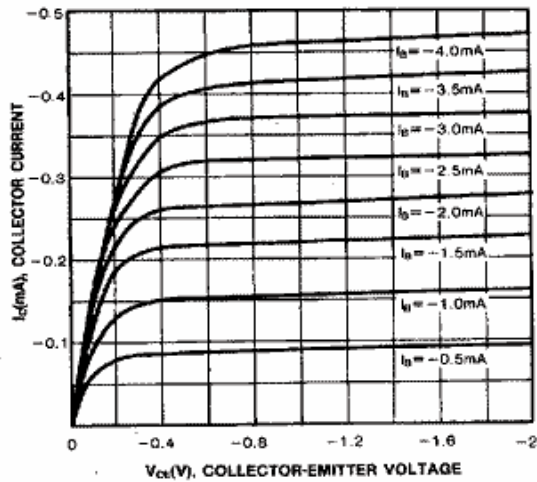
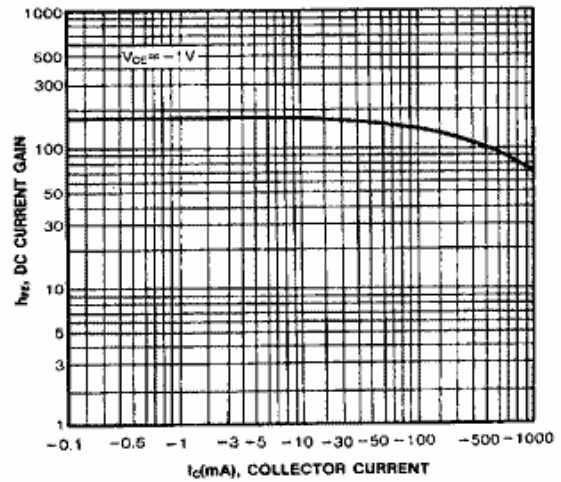
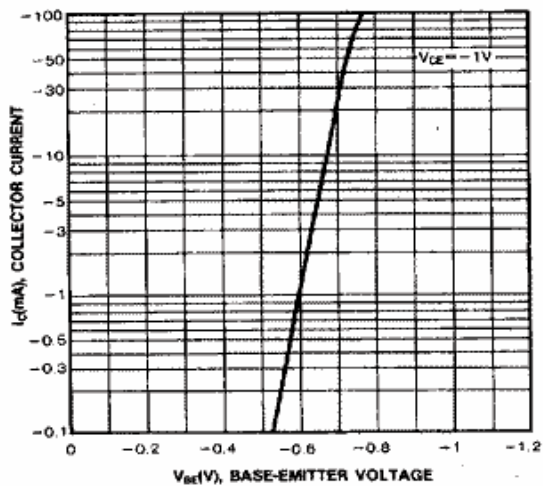
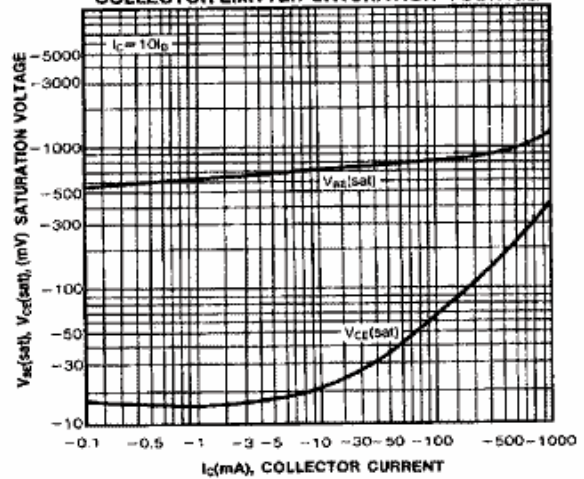
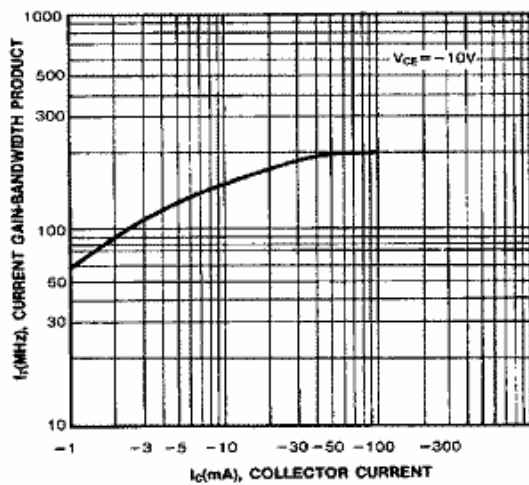
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1.5	A
P _C	Collector Power Dissipation	0.3	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-0.1mA, I _B =0	-25		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0		-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-20V, I _B =0		-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0		-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	120	400	
	h _{FE(2)}	V _{CE} =-1V, I _C =-800mA	40		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B =-80mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA		-1.2	V
Base-emitter on voltage	V _{BE(on)}	I _C =-1V, V _{CE} =-10mA		-1	V
Base-emitter positive forward voltage	V _{BEF}	I _B =-1A		-1.55	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -50mA f=30MHz	100		MHz
output capacitance	C _{ob}	(V _{CB} =-10V, I _E =0, f=1MHz)		20	pF

CLASSIFICATION OF h_{FE(1)}

Rank	L	H	J
Range	120-200	200-350	300-400

STATIC CHARACTERISTIC

DC CURRENT GAIN

BASE-EMITTER ON VOLTAGE

**BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE**

CURRENT GAIN-BANDWIDTH PRODUCT

COLLECTOR OUTPUT CAPACITANCE
